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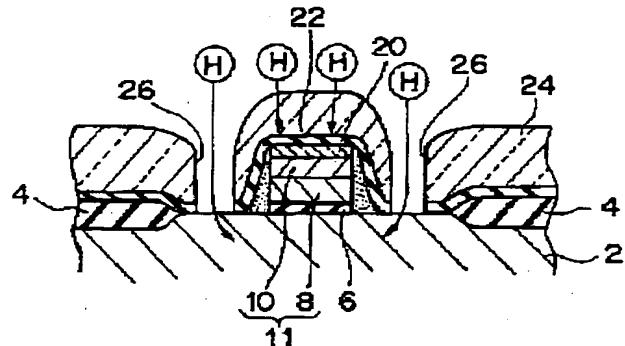
APPLICATION DATE : 26-07-94
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APPLICANT : SONY CORP;

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TITLE : SEMICONDUCTOR DEVICE AND ITS
 MANUFACTURE



ABSTRACT : PURPOSE: To enable a transistor to be protected against moisture or phosphorus that penetrates into it through an interlayer film and completely hydrogenated.

CONSTITUTION: A hydrogen supplying source layer 20 which serves as an antireflection layer when a gate electrode 11 is subjected to photolithography processing is provided onto the gate electrode 11 of a transistor. It is preferable that the hydrogen supplying source layer 20 is formed of hydrogen-containing SiO_xNy film or hydrogen-containing Si_xNy film. It is preferable that a barrier layer 22 is provided onto the hydrogen supplying source layer 20. It is preferable that the barrier layer 22 is formed of silicon nitride film prepared through a low-pressure CVD method or an ECR-CVD method. An interlayer film 24 is formed on the barrier layer 22.

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